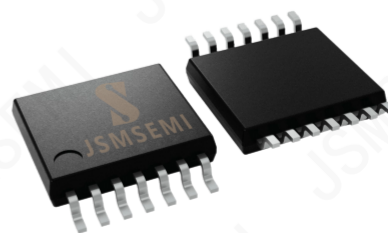


1、General Description

The SN74LVC08APWR-JSM provides four 2-input AND gates. Inputs can be driven from either 3.3V or 5V devices. This feature allows the use of these devices as translators in mixed 3.3V and 5V applications.



Features:

- 5V tolerant inputs for interfacing with 5V logic
- Wide supply voltage range from 1.2V to 3.6V
- CMOS low power consumption
- Direct interface with TTL levels
- Specified from -40°C to +125°C
- Packaging information: TSSOP14

2、Block Diagram And Pin Description

2.1、Block Diagram

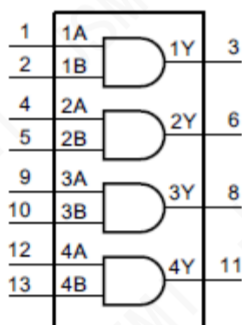


Figure 1. Logic symbol

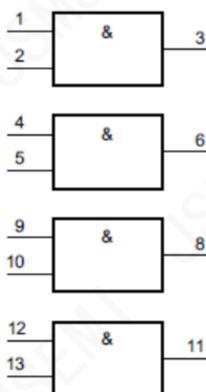


Figure 2. IEC logic symbol

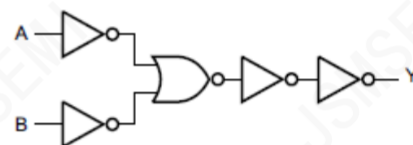
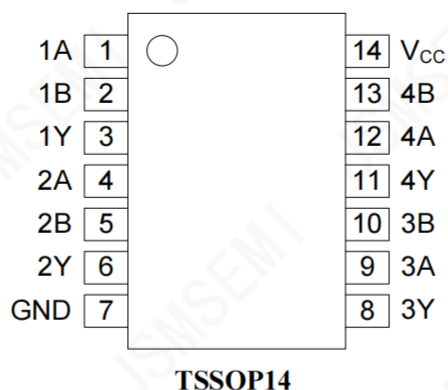


Figure 3. Logic diagram for one gate

Ordering Information

Order number	Package	Operation Temperature Range	MSL Grade	Ship, Quantity	Green
SN74LVC08APWR-JSM	TSSOP14	-40 to 125° C	3	T&R,2500	RoHS

2.2、Pin Configurations



2.3、Pin Description

Pin No. TSSOP14	Pin Name	Description
1	1A	data input
2	1B	data input
3	1Y	data output
4	2A	data input
5	2B	data input
6	2Y	data output
7	GND	ground (0V)
8	3Y	data output
9	3A	data input
10	3B	data input
11	4Y	data output
12	4A	data input
13	4B	data input
14	V _{CC}	supply voltage

2.4、Function Table

Input		Output
nA	nB	nY
L	X	L
X	L	L
H	H	H

Note: H=HIGH voltage level; L=LOW voltage level; X=don't care.

3、Electrical Parameter

3.1、Absolute Maximum Ratings

(Voltages are referenced to GND(ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Max.	Unit
supply voltage	V_{CC}	-	-0.5	+6.5	V
input clamping current	I_{IK}	$V_I < 0V$	-50	-	mA
input voltage	V_I	-	-0.5	+6.5	V
output clamping current	I_{OK}	$V_O > V_{CC}$ or $V_O < 0V$	-	± 50	mA
output voltage	V_O	output in HIGH or LOW-state	-0.5	$V_{CC}+0.5$	V
output current	I_O	$V_O=0V$ to V_{CC}	-	± 50	mA
supply current	I_{CC}	-	-	100	mA
ground current	I_{GND}	-	-100	-	mA
total power dissipation	P_{tot}	-	-	500	mW
storage temperature	T_{stg}	-	-65	+150	°C
soldering Temperature	T_L	10s	260		°C

3.2、Recommended Operating Conditions

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
supply voltage	V_{CC}	-	1.65	-	3.6	V
		functional	1.2	-	-	V
input voltage	V_I	-	0	-	5.5	V
output voltage	V_O	output HIGH or LOW state	0	-	V_{CC}	V
ambient temperature	T_{amb}	-	-40	-	+125	°C
input transition rise and fall rate	$\Delta t/\Delta V$	$V_{CC}=1.65V$ to $2.7V$	0	-	20	ns/V
		$V_{CC}=2.7V$ to $3.6V$	0	-	10	ns/V

3.3、Electrical Characteristics

3.3.1、DC Characteristics 1

($T_{amb} = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Unit
HIGH-level input voltage	V_{IH}	$V_{CC}=1.2\text{V}$		1.08	-	-	V
		$V_{CC}=1.65\text{V to }1.95\text{V}$		$0.65 \times V_{CC}$	-	-	V
		$V_{CC}=2.3\text{V to }2.7\text{V}$		1.7	-	-	V
		$V_{CC}=2.7\text{V to }3.6\text{V}$		2.0	-	-	V
LOW-level input voltage	V_{IL}	$V_{CC}=1.2\text{V}$		-	-	0.12	V
		$V_{CC}=1.65\text{V to }1.95\text{V}$		-	-	$0.35 \times V_{CC}$	V
		$V_{CC}=2.3\text{V to }2.7\text{V}$		-	-	0.7	V
		$V_{CC}=2.7\text{V to }3.6\text{V}$		-	-	0.8	V
HIGH-level output voltage	V_{OH}	$V_I = V_{IH} \text{ or } V_{IL}$	$I_O = -100\mu\text{A}; V_{CC}=1.65\text{V to }3.6\text{V}$	$V_{CC} - 0.2$	-	-	V
			$I_O = -4\text{mA}; V_{CC}=1.65\text{V}$	1.2	-	-	V
			$I_O = -8\text{mA}; V_{CC}=2.3\text{V}$	1.8	-	-	V
			$I_O = -12\text{mA}; V_{CC}=2.7\text{V}$	2.2	-	-	V
			$I_O = -18\text{mA}; V_{CC}=3.0\text{V}$	2.4	-	-	V
			$I_O = -24\text{mA}; V_{CC}=3.0\text{V}$	2.2	-	-	V
LOW-level output voltage	V_{OL}	$V_I = V_{IH} \text{ or } V_{IL}$	$I_O = 100\mu\text{A}; V_{CC}=1.65\text{V to }3.6\text{V}$	-	-	0.2	V
			$I_O = 4\text{mA}; V_{CC}=1.65\text{V}$	-	-	0.45	V
			$I_O = 8\text{mA}; V_{CC}=2.3\text{V}$	-	-	0.6	V
			$I_O = 12\text{mA}; V_{CC}=2.7\text{V}$	-	-	0.4	V
			$I_O = 24\text{mA}; V_{CC}=3.0\text{V}$	-	-	0.55	V
input leakage current	I_I	$V_I = 5.5\text{V or GND}; V_{CC}=3.6\text{V}$		-	-	± 5	μA
supply current	I_{CC}	$V_I = V_{CC} \text{ or GND}; I_O = 0\text{A}; V_{CC}=3.6\text{V}$		-	-	15	μA
additional supply current	ΔI_{CC}	per input pin; $V_I = V_{CC} - 0.6\text{V}; I_O = 0\text{A}; V_{CC}=2.7\text{V to }3.6\text{V}$		-	-	500	μA
input capacitance	C_I	$V_{CC}=0\text{V to }3.6\text{V}; V_I = \text{GND to } V_{CC}$		-	4.0	-	pF

Note: All typical values are measured at $V_{CC}=3.3\text{V}$ (unless stated otherwise) and $T_{amb}=25^{\circ}\text{C}$.

3.3.2、DC Characteristics 2

($T_{amb} = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
HIGH-level input voltage	V_{IH}	$V_{CC}=1.2\text{V}$	1.08	-	-	V
		$V_{CC}=1.65\text{V}$ to 1.95V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC}=2.3\text{V}$ to 2.7V	1.7	-	-	V
		$V_{CC}=2.7\text{V}$ to 3.6V	2.0	-	-	V
LOW-level input voltage	V_{IL}	$V_{CC}=1.2\text{V}$	-	-	0.12	V
		$V_{CC}=1.65\text{V}$ to 1.95V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC}=2.3\text{V}$ to 2.7V	-	-	0.7	V
		$V_{CC}=2.7\text{V}$ to 3.6V	-	-	0.8	V
HIGH-level output voltage	V_{OH}	$V_I = V_{IH} \text{ or } V_{IL}$	$I_O = -100\mu\text{A}; V_{CC}=1.65\text{V}$ to 3.6V	$V_{CC} - 0.3$	-	V
			$I_O = -4\text{mA}; V_{CC}=1.65\text{V}$	1.05	-	V
			$I_O = -8\text{mA}; V_{CC}=2.3\text{V}$	1.65	-	V
			$I_O = -12\text{mA}; V_{CC}=2.7\text{V}$	2.05	-	V
			$I_O = -18\text{mA}; V_{CC}=3.0\text{V}$	2.25	-	V
			$I_O = -24\text{mA}; V_{CC}=3.0\text{V}$	2.0	-	V
LOW-level output voltage	V_{OL}	$V_I = V_{IH} \text{ or } V_{IL}$	$I_O = 100\mu\text{A}; V_{CC}=1.65\text{V}$ to 3.6V	-	0.3	V
			$I_O = 4\text{mA}; V_{CC}=1.65\text{V}$	-	0.65	V
			$I_O = 8\text{mA}; V_{CC}=2.3\text{V}$	-	0.8	V
			$I_O = 12\text{mA}; V_{CC}=2.7\text{V}$	-	0.6	V
			$I_O = 24\text{mA}; V_{CC}=3.0\text{V}$	-	0.8	V
input leakage current	I_I	$V_I = 5.5\text{V}$ or GND; $V_{CC}=3.6\text{V}$	-	-	± 20	μA
supply current	I_{CC}	$V_I = V_{CC}$ or GND; $I_O = 0\text{A}; V_{CC}=3.6\text{V}$	-	-	200	μA
additional supply current	ΔI_{CC}	per input pin; $V_I = V_{CC} - 0.6\text{V}; I_O = 0\text{A}; V_{CC}=2.7\text{V}$ to 3.6V	-	-	5000	μA

Note: All typical values are measured at $V_{CC}=3.3\text{V}$ (unless stated otherwise) and $T_{amb}=25^{\circ}\text{C}$.

3.3.3、AC Characteristics 1

($T_{amb}=-40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
nA, nB to nY propagation delay	t_{pd}	see Figure 5	$V_{CC}=1.2\text{V}$	-	11.0	ns
			$V_{CC}=1.65\text{V to }1.95\text{V}$	0.5	4.2	ns
			$V_{CC}=2.3\text{V to }2.7\text{V}$	1.0	2.5	ns
			$V_{CC}=2.7\text{V}$	1.5	2.5	ns
			$V_{CC}=3.0\text{V to }3.6\text{V}$	1.0	2.3	ns
output skew time	$t_{sk(o)}$	$V_{CC}=3.0\text{V to }3.6\text{V}$	-	-	1.0	ns
Power dissipation capacitance	C_{PD}	per gate; $V_I = \text{GND to } V_{CC}$	$V_{CC}=1.65\text{V to }1.95\text{V}$	-	4.4	pF
			$V_{CC}=2.3\text{V to }2.7\text{V}$	-	7.7	pF
			$V_{CC}=3.0\text{V to }3.6\text{V}$	-	10.5	pF

Note:

[1] Typical values are measured at $T_{amb}=25^{\circ}\text{C}$ and $V_{CC}=1.2\text{V}, 1.8\text{V}, 2.5\text{V}, 2.7\text{V}$ and 3.3V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in uW).

$P_D=(C_{PD}\times V_{CC}^2\times f_i\times N)+\sum(C_L\times V_{CC}^2\times f_o)$ where:

f_i =input frequency in MHz;

f_o =output frequency in MHz;

C_L =output load capacitance in pF;

V_{CC} =supply voltage in V;

N =number of inputs switching;

$\sum(C_L\times V_{CC}^2\times f_o)$ =sum of outputs.

3.3.4、AC Characteristics 2

($T_{amb}=-40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
nA, nB to nY propagation delay	t_{pd}	see Figure 5	$V_{CC}=1.65\text{V to }1.95\text{V}$	0.5	-	10.4 ns
			$V_{CC}=2.3\text{V to }2.7\text{V}$	1.0	-	8.0 ns
			$V_{CC}=2.7\text{V}$	1.5	-	5.6 ns
			$V_{CC}=3.0\text{V to }3.6\text{V}$	1.0	-	4.8 ns
output skew time	$t_{sk(o)}$	$V_{CC}=3.0\text{V to }3.6\text{V}$	-	-	1.5	ns

Note:

[1] Typical values are measured at $T_{amb}=25^{\circ}\text{C}$ and $V_{CC}=1.2\text{V}, 1.8\text{V}, 2.5\text{V}, 2.7\text{V}$ and 3.3V respectively.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

4、Testing Circuit

4.1、AC Testing Circuit

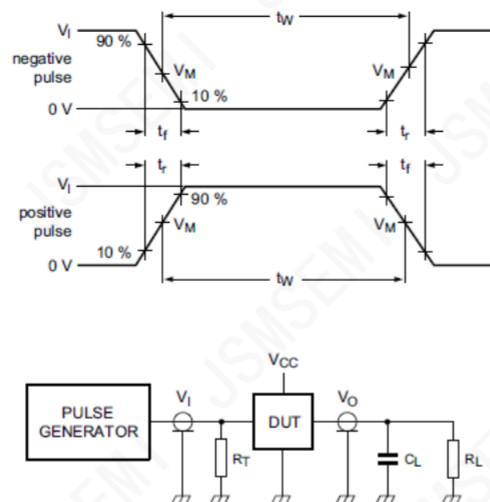


Figure 4. Test circuit for measuring switching times

Definitions for test circuit:

R_L =Load resistance.

C_L =Load capacitance including jig and probe capacitance.

R_T =Termination resistance should be equal to the output impedance Z_o of the pulse generator.

4.2、AC Testing Waveforms

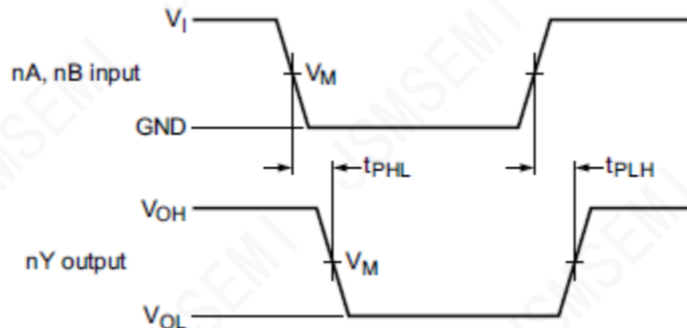


Figure 5. The input (nA, nB) to output (nY) propagation delays

4.3、Measurement Points

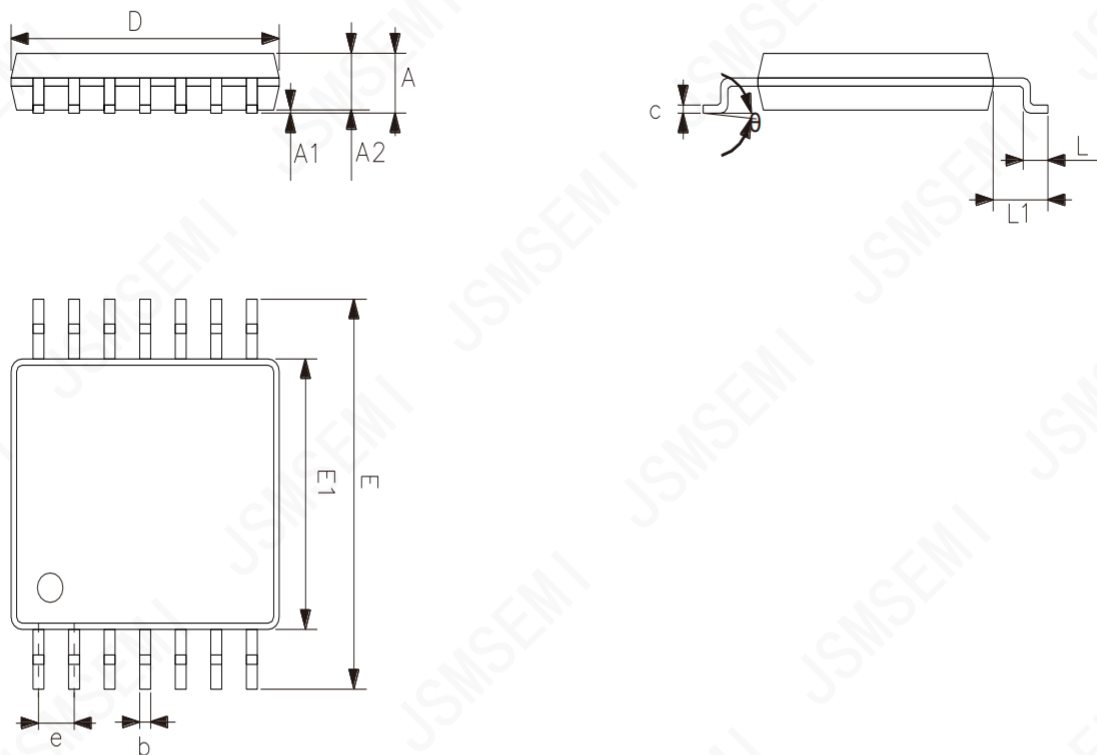
Supply voltage	Input	Output
V_{CC}	V_M	V_M
$< 2.7V$	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
$\geq 2.7V$	1.5V	1.5V

4.4、Test Data

Supply voltage	Input		Load	
V_{CC}	V_I	t_r, t_f	C_L	R_L
1.2V	V_{CC}	$\leq 2.0ns$	30pF	1k Ω
1.65V to 1.95V	V_{CC}	$\leq 2.0ns$	30pF	1k Ω
2.3V to 2.7V	V_{CC}	$\leq 2.0ns$	30pF	500 Ω
2.7V	2.7V	$\leq 2.5ns$	50pF	500 Ω
3.0V to 3.6V	2.7V	$\leq 2.5ns$	50pF	500 Ω

5、Package Information

5.1、TSSOP14



2023/12/A	Dimensions In Millimeters	
Symbol	Min	Max
A	—	1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	4.90	5.10
E1	4.30	4.50
E	6.20	6.60
e	0.65	
L	0.45	0.75
L1	1.00	
θ	0°	8°

6、Statements And Notes

6.1、The name and content of Hazardous substances or Elements in the product

Part name	Hazardous substances or Elements									
	Lead and lead compounds	Mercury and mercury compounds	Cadmium and cadmium compounds	Hexavalent chromium compounds	Polybrominated biphenyls	Polybrominated biphenyl ethers	Dibutyl phthalate	Butylbenzyl phthalate	Di-2-ethylhexyl phthalate	Diisobutyl phthalate
Lead frame	○	○	○	○	○	○	○	○	○	○
Plastic resin	○	○	○	○	○	○	○	○	○	○
Chip	○	○	○	○	○	○	○	○	○	○
The lead	○	○	○	○	○	○	○	○	○	○
Plastic sheet installed	○	○	○	○	○	○	○	○	○	○
explanation	○: Indicates that the content of hazardous substances or elements in the detection limit of the following the SJ/T11363-2006 standard. ×: Indicates that the content of hazardous substances or elements exceeding the SJ/T11363-2006 Standard limit requirements.									

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